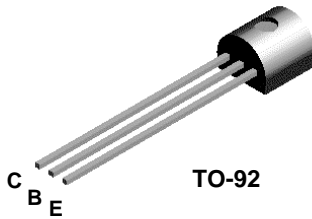
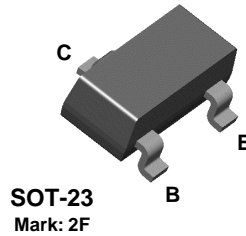


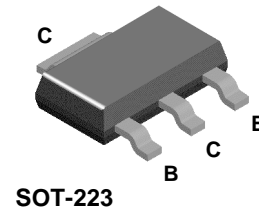
## PN2907A



## MMBT2907A



## PZT2907A



## PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 63.

### Absolute Maximum Ratings\*

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_C$	Collector Current - Continuous	800	mA
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

### Thermal Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Characteristic	Max			Units
		PN2907A	*MMBT2907A	**PZT2907A	
$P_D$	Total Device Dissipation	625	350	1,000	mW
	Derate above $25^\circ\text{C}$	5.0	2.8	8.0	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	$^\circ\text{C}/\text{W}$

\* Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

\*\* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

# PNP General Purpose Amplifier

(continued)

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
<b>OFF CHARACTERISTICS</b>					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10\text{ mA}, I_B = 0$	60		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\ \mu\text{A}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\ \mu\text{A}, I_C = 0$	5.0		V
$I_B$	Base Cutoff Current	$V_{CB} = 30\text{ V}, V_{EB} = 0.5\text{ V}$		50	nA
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = 30\text{ V}, V_{BE} = 0.5\text{ V}$		50	nA
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 50\text{ V}, I_E = 0$ $V_{CB} = 50\text{ V}, I_E = 0, T_A = 150^\circ\text{C}$		0.02 20	$\mu\text{A}$ $\mu\text{A}$

## ON CHARACTERISTICS

$h_{FE}$	DC Current Gain	$I_C = 0.1\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}, V_{CE} = 10\text{ V}^*$ $I_C = 500\text{ mA}, V_{CE} = 10\text{ V}^*$	75 100 100 100 50	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$		0.4 1.6	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150\text{ mA}, I_B = 15\text{ mA}^*$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$		1.3 2.6	V V

## SMALL SIGNAL CHARACTERISTICS

$f_T$	Current Gain - Bandwidth Product	$I_C = 50\text{ mA}, V_{CE} = 20\text{ V},$ $f = 100\text{ MHz}$	200		MHz
$C_{obo}$	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0,$ $f = 100\text{ kHz}$		8.0	pF
$C_{ibo}$	Input Capacitance	$V_{EB} = 2.0\text{ V}, I_C = 0,$ $f = 100\text{ kHz}$		30	pF

## SWITCHING CHARACTERISTICS

$t_{on}$	Turn-on Time	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA},$ $I_{B1} = 15\text{ mA}$		45	ns
$t_d$	Delay Time			10	ns
$t_r$	Rise Time			40	ns
$t_{off}$	Turn-off Time	$V_{CC} = 6.0\text{ V}, I_C = 150\text{ mA}$ $I_{B1} = I_{B2} = 15\text{ mA}$		100	ns
$t_s$	Storage Time			80	ns
$t_f$	Fall Time			30	ns

\*Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

**NOTE:** All voltages (V) and currents (A) are negative polarity for PNP transistors.

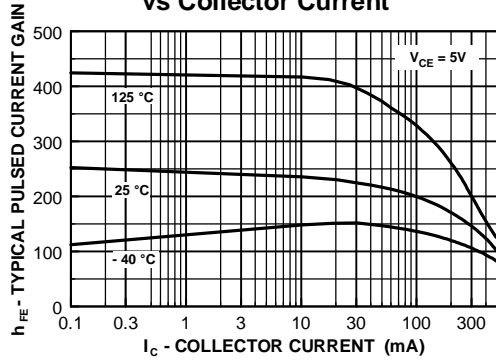
## Spice Model

PNP (Is=650.6E-18 Xti=3 Eg=1.11 Vaf=115.7 Bf=231.7 Ne=1.829 Ise=54.81f Ikf=1.079 Xtb=1.5 Br=3.563 Nc=2 Isc=0 Ikr=0 Rc=.715 Cjc=14.76p Mjc=.5383 Vjc=.75 Fc=.5 Cje=19.82p Mje=.3357 Vje=.75 Tr=111.3n Tf=603.7p ltf=.65 Vtf=5 Xtf=1.7 Rb=10)

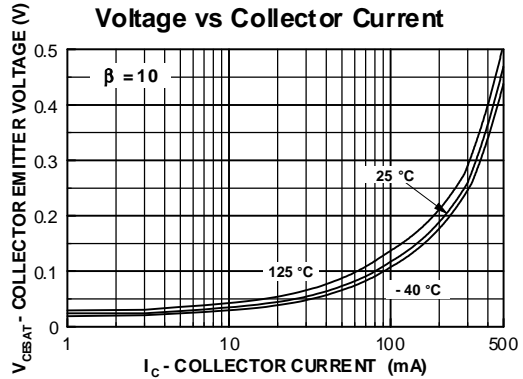
PN2907A / MMBT2907A / PZT2907A

Typical Characteristics

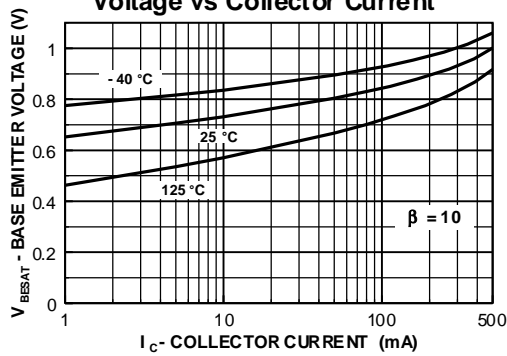
Typical Pulsed Current Gain vs Collector Current



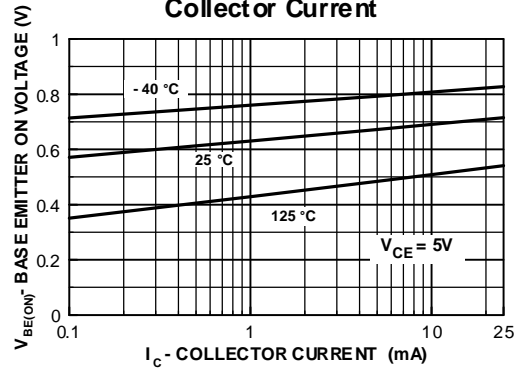
Collector-Emitter Saturation Voltage vs Collector Current



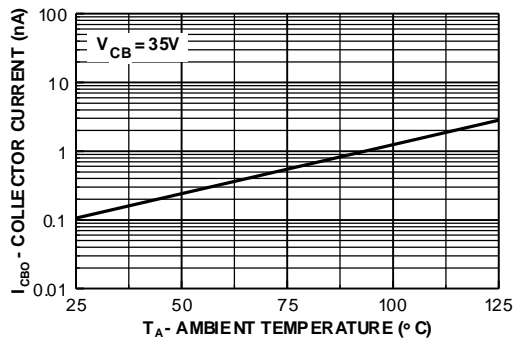
Base-Emitter Saturation Voltage vs Collector Current



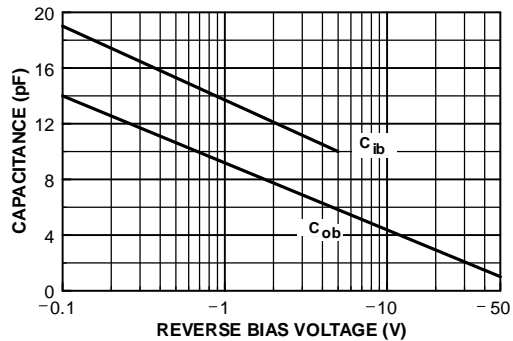
Base Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature



Input and Output Capacitance vs Reverse Bias Voltage

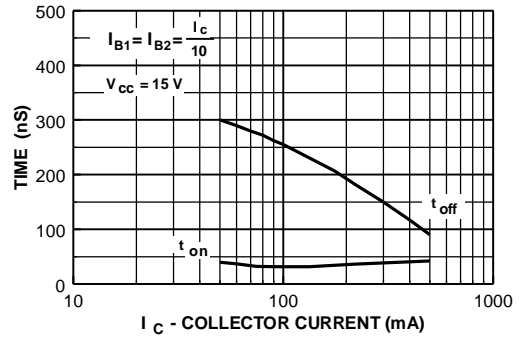


Typical Characteristics (continued)

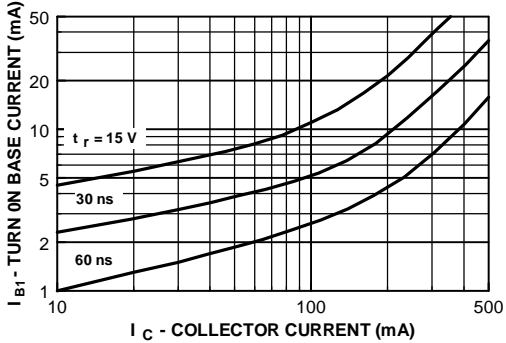
Switching Times vs Collector Current



Turn On and Turn Off Times vs Collector Current



Rise Time vs Collector and Turn On Base Currents



Power Dissipation vs Ambient Temperature



Typical Common Emitter Characteristics (f = 1.0kHz)



Test Circuits

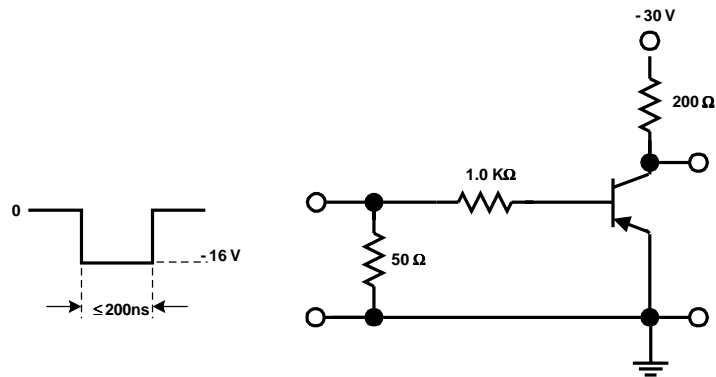


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

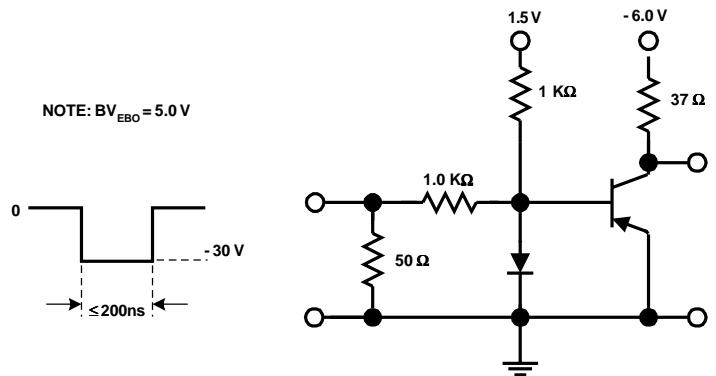


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

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DOME™	ISOPLANAR™	Quiet Series™	
E <sup>2</sup> CMOS™	MICROWIRE™	SILENT SWITCHER®	
EnSigna™	OPTOLOGIC™	SMART START™	
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FACT Quiet Series™	PACMAN™	SuperSOT™-6	
FAST®	POP™	SuperSOT™-8	

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